

11th RD50 Workshop

Tuesday, 13 November 2007

Defect and Material Characterization & New Materials - 40-S2-C01 (13:30 - 18:10)

| time | [id] title | presenter |
|-------|-------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------|
| 13:30 | [13] The WODEAN Project | FRETWURST, Eckhart |
| 13:50 | [12] Cluster related hole traps with enhanced-electric-field-emission- the source for long term annealing in hadron irradiated silicon diodes - | PINTILIE, Ioana |
| 14:10 | [18] Annealing studies on defects after neutron irradiation in different silicon material | Ms JUNKES, Alexandra |
| 14:30 | [20] INTERPRETATION OF DLTS DATA FOR SILICON DETECTORS IRRADIATED WITH NEUTRONS | Dr MAKARENKO, Leonid |
| 15:00 | Coffee break | |
| 15:30 | [9] Annealing induced evolution of defect centres in MCz silicon irradiated with a neutron fluence of $1e16 \text{ cm}^{-2}$ | Prof. KAMINSKI, Pawel |
| 15:50 | [6] Fluence dependent recombination lifetime in neutron and proton irradiated MCz , FZ and epi-Si structures. | Dr GAUBAS, Eugenijus |
| 16:10 | [10] Photoconductivity spectra and persistent conductivity in the irradiated Si samples (WODEAN) | VAITKUS, Juozas |
| 16:30 | [28] Characteristics of InP Particle Detectors Structures | Prof. SOPKO, Bruno |
| 16:50 | [14] Discussion Session: Defect and Material Characterization | |